

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ELM/001 Cont. 15	APPLN. NO. 10/766,629
O I P E SEP 10 2004 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANTS Glenn J. Leedy	CONF. NO. 3771
		FILING DATE January 27, 2004	GROUP ART UNIT 1766 2818

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TJL	4,500,905	02/19/1985	Shibata	357	68	
	4,939,568	07/03/1990	Kato, et al.	357	75	
	4,892,753	01/09/1990	Wang, et al.	427	579	
	5,000,113	03/19/1991	Wang, et al.	118	723	
	5,240,458	08/31/1993	Linglain, et al.	464	63	
	5,259,247	11/09/1993	Bantien	73	718	
	RE 34,893	04/04/1995	Fujii, et al.	257	419	
	RE 36,623	03/21/2000	Wang, et al.	427	579	
	6,087,284	07/11/2000	Brix, et al.	501	69	
TJL	6,518,073	02/11/2003	Momohara	438	4	12/10/2001

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
TJL	04-196,263	07/1992	Japan			(Abs)	

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

EXAMINER INITIAL	
TJL	Aboaf, J.A., "Stresses in SiO <sub>2</sub> Films Obtained from the Thermal Decomposition of Tetraethylorthosilicate – Effect of Heat Treatment and Humidity," J. Electrochem. Soc.: Solid State Science; 116(12): 1732-1736 (Dec. 1969).
	Scheuerman, R.J., "Fabrication of Thin Dielectric Films with Low Internal Stresses," J. Vac. Sci. and Tech., 7(1): 143-146 (1970).
	Bailey, R., "Glass for Solid-State Devices: Glass film has low intrinsic compressive stress for isolating active layers of magnetic-bubble and other solid-state devices," NASA Tech Brief (1982).
	"Partitioning Function and Packaging of Integrated Circuits for Physical Security of Data," IBM Technical Disclosure Bulletin, IBM Corp.; 32(1): 46-49 (June 1989).
	Hsieh, et al., "Directional Deposition of Dielectric Silicon Oxide by Plasma Enhanced TEOS Process," 1989 Proceedings, Sixth International IEEE VLSI Multilevel Interconnection Conference, pp. 411-415 (1989).
TJL	Tessier, et al., "An Overview of Dielectric Materials for Multichip Modules," SPE, Electrical & Electronic Div.; (6): 260-269 (1991).

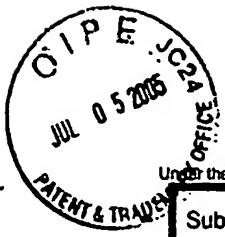
EXAMINER

TJL-TJL-HO

DATE CONSIDERED

Nov 2005

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.



PTO/SB/08A (10-01)

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**Complete if known**

Application Number	10/766,629 (Conf. No.: 3771)
Filing Date	January 27, 2004
First Named Inventor	Glenn J. Leedy
Art Unit	2818
Examiner Name	Thinh T. Nguyen
Attorney Docket Number	ELM-1 CONT.15

**INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 1 of 1

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
TH		4,724,328	02/09/1988	Lischke	
		4,994,336	02/19/1991	Benecke et al.	
		5,358,909	10/25/1994	Hashiguchi et al.	
		5,514,628	05/07/1996	Enomoto et al.	
TH		5,620,915	04/15/1997	Chen et al.	

**FOREIGN PATENT DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>4</sup> - Number <sup>5</sup> - kind code <sup>6</sup>				
TH		GB 2,125,168	02/29/1984	Kouno		
TH		JP 02-037655	02/07/1990	Benecke et al.		

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>3</sup>
TH		"Christensens Physics of Diagnostic Radiology," Curry et al., pp.29-33, 1990...	

Examiner Signature

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Date Considered

NOV 2005

All References Have Been Considered:  
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Examiner \_\_\_\_\_

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